

— 115 —

34. *Enallagma*

7. Hydroxyl is only 44%

Feb, 2005

- ☛ Drafts
  - ☛ BRS:
  - ☛ BRS:
  - ☛ BRS:
  - ☛ BRS: knall
  - ☛ BRS: 19 21 23
  - ☛ BRS: 32with 33
  - ☛ BRS:
- ☛ Pending
- ☛ Active
  - ☛ L1: (44): (((barrier near (height tunnel)) tunnel\$4 ((energy diagram co
- ☛ Failed
- ☛ Saved
  - ☛ S1: (1) 09/948877
  - ☛ S2: (1738) "KONINKLIJKE PHILIPS".as.
  - ☛ S3: (175943) ((barrier near (height tunnel)) tunnel\$4 ((energy diagr
  - ☛ S4: (39120) ((barrier near (height tunnel\$4)) ((energy diagram cond
  - ☛ S5: (8062820) different second
  - ☛ S6: (1448) (different second) adj (((barrier near (height tunnel\$4)) ((
  - ☛ S7: (43918) float\$4 adj (gate electrode plate trap\$4) FG
  - ☛ S8: (187632) (control adj (gate electrode plate) CG word adj line wordli
  - ☛ S9: (8) ((different second) adj (((barrier near (height tunnel\$4)) ((en
  - ☛ S10: (11) ((different second) adj (((barrier near (height tunnel\$4)) ((
  - ☛ S11: (14) ((different second) adj (((barrier near (height tunnel\$4)) ((

	U	I	Inventor	Document	Issue P	Title	Current	Current X	Retrieval S	C	P	3	4	Image Doc P
1	✓	□	Chindalore, US	200301	2003 : 6	Non-volatile memory device with impro	438/20	257/E29.1		□	□	□	□	US 20030
2	✓	□	Nakazato, US	657414	2003 : 1	Memory device using hot charge carri	365/18	257/315.		□	□	□	□	US 65741
3	□	□	Forbes, Le	US 200500	2005 : 2	Write once read only memory with larg	385/18			□	□	□	□	US 20050
4	✓	□	Rudeck, Pa	US 200500	2005 : 2	Methods and structure for an improve	438/26	438/260.		□	□	□	□	US 20050
5	✓	□	Chindalore, US	200401	2004 : 6	Non-volatile memory device with improv	257/32	257/321.		□	□	□	□	US 20040
6	✓	□	Hyde, John	US 200400	2004 : 3	Pseudo-nonvolatile direct-tunneling flo	257/31	257/E29.3		□	□	□	□	US 20040
7	✓	□	Forbes, Le	US 200302	2003 : 2	Write once read only memory with larg	257/31	257/314.		□	□	□	□	US 20030
8	✓	□	Rudeck, Pa	US 200302	2003 : 2	Method and structure for an improved	438/20	257/E21.6		□	□	□	□	US 20030
9	✓	□	Mihnea, An	US 200300	2003 : 1	Flash memory cell for high efficiency p	365/18	365/185.0		□	□	□	□	US 20030
10	✓	□	Mihnea, An	US 200300	2003 : 1	Flash memory cell for high efficiency p	365/18			□	□	□	□	US 20030